### **Digital Transistors (BRT)** R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

### **NPN Transistors with Monolithic Bias Resistor Network**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	$V_{CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	12	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

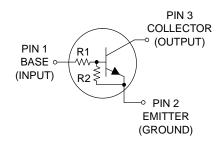
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



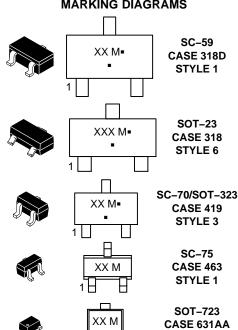
#### ON Semiconductor®

#### www.onsemi.com

#### PIN CONNECTIONS



#### **MARKING DIAGRAMS**



= Specific Device Code XXX

= Date Code\* = Pb-Free Package

IX ME 1

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

STYLE 1 SOT-1123

**CASE 524AA** STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2231T1G	8H	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2231LT1G, NSVMMUN2231LT1G*	A8H	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5231T1G	8H	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC123EET1G	8H	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC123EM3T5G, NSVDTC123EM3T5G*	8H	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC123EF3T5G	E (180°)**	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

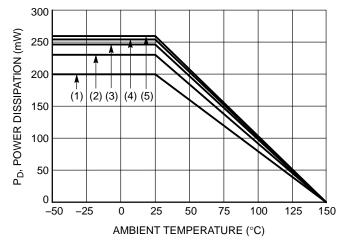


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

<sup>\*</sup>NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

\*\* (xx°) = Degree rotation in the clockwise direction.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2231)		-		
Total Device Dissipation		P <sub>D</sub>		
$T_A = 25^{\circ}C$	(Note 1)		230	mW
Derate above 25°C	(Note 2) (Note 1)		338 1.8	mW/°C
2014.0 42010 20 0	(Note 2)		2.7	
Thermal Resistance,	(Note 1)	$R_{\theta JA}$	540	°C/W
Junction to Ambient	(Note 2)		370	
Thermal Resistance,	(Note 1)	$R_{ hetaJL}$	264	°C/W
Junction to Lead	(Note 2)		287	
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2231L)				
Total Device Dissipation	(NI=(= 4)	$P_{D}$	0.40	14/
$T_A = 25^{\circ}C$	(Note 1) (Note 2)		246 400	mW
Derate above 25°C	(Note 1)		2.0	mW/°C
	(Note 2)		3.2	
Thermal Resistance,	(Note 1)	$R_{ heta JA}$	508	°C/W
Junction to Ambient	(Note 2)		311	
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	174 208	°C/W
	(Note 2)			00
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5231)			1	
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1)	$P_{D}$	202	mW
1 <sub>A</sub> = 23 0	(Note 2)		310	11100
Derate above 25°C	(Note 1)		1.6	mW/°C
	(Note 2)		2.5	
Thermal Resistance,	(Note 1)	$R_{ heta JA}$	618	°C/W
Junction to Ambient	(Note 2)		403	2014
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range	(***** =/	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTC123EE)	<del>]</del>	· J, ·stg	00 10 1 100	
Total Device Dissipation		D-	T	
T <sub>A</sub> = 25°C	(Note 1)	$P_{D}$	200	mW
	(Note 2)		300	
Derate above 25°C	(Note 1) (Note 2)		1.6 2.4	mW/°C
Thermal Resistance,	(Note 1)	D	600	°C/W
Junction to Ambient	(Note 1)	$R_{ heta JA}$	400	C/VV
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTC123EM3)		0.019	l	
Total Device Dissipation		P <sub>D</sub>	Ī	
T <sub>A</sub> = 25°C	(Note 1)	D	260	mW
Doubte also see OFOC	(Note 2)		600	
Derate above 25°C	(Note 1) (Note 2)		2.0 4.8	mW/°C
Thermal Desistance				0000
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	480 205	°C/W
	(	т. т	-55 to +150	°C
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 tO +15U	

- 1. FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 lnch Pad.
   FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic	Symbol	Max	Unit	
THERMAL CHARACTERISTICS (SOT-1123) (NSBC123EF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ heta JA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ hetaJL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- 3. FR-4 @ 100 mm², 1 oz. copper traces, still air. 4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

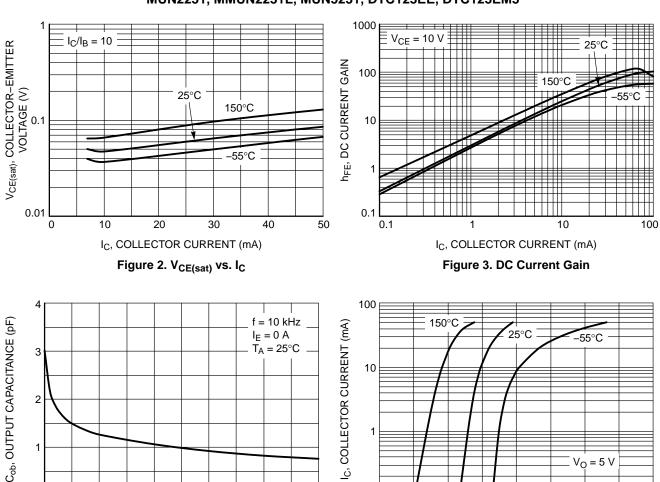
**Table 3. ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	_	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	-	2.3	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \mu A, I_E = 0)$	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	8.0	15	-	
Collector–Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 5.0 mA)	V <sub>CE(sat)</sub>	_	-	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A})$	$V_{i(off)}$	_	1.2	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_C = 20 \text{ mA})$	V <sub>i(on)</sub>	2.0	1.7	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	-	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	1.5	2.2	2.9	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>5.</sup> Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

#### TYPICAL CHARACTERISTICS MUN2231, MMUN2231L, MUN5231, DTC123EE, DTC123EM3



0.1

0

1

V<sub>R</sub>, REVERSE VOLTAGE (V) Figure 4. Output Capacitance

30

40

20

0

0

10

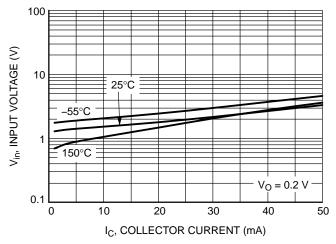
V<sub>in</sub>, INPUT VOLTAGE (V) Figure 5. Output Current vs. Input Voltage

2

 $V_O = 5 V$ 

3

4



50

Figure 6. Input Voltage vs. Output Current

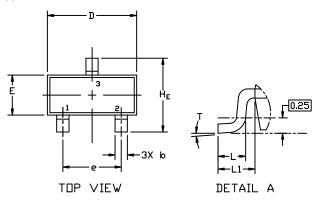




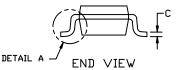
**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

#### SCALE 4:1





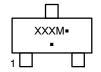


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIM	ETERS			INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

# GENERIC MARKING DIAGRAM\*

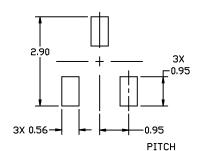


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposition Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

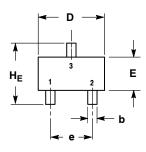
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

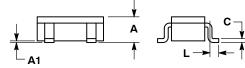




SC-59 CASE 318D-04 ISSUE H

**DATE 28 JUN 2012** 





#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code М

= Pb-Free Package\*

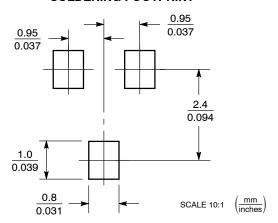
(\*Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
С	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118

#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

CTVIE 2

PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE
2. EMITTER	2. N.C.	2. ANODE
3. COLLECTOR	3. CATHODE	3. CATHODE
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. CATHODE	PIN 1. CATHODE	PIN 1. ANODE
2. N.C.	2. CATHODE	2. CATHODE
3. ANODE	3. ANODE	3. ANODE/CATHODE

CTVIE 2

DOCUMENT NUMBER:	98ASB42664B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	SC-59		PAGE 1 OF 1

QTVI E 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.





SC-70 (SOT-323) **CASE 419** ISSUE R

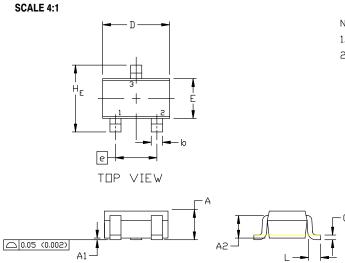
END VIEW

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



#### **GENERIC MARKING DIAGRAM**

SIDE VIEW

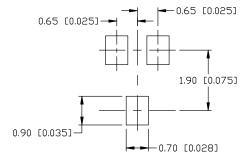


= Specific Device Code XX

М = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER	STYLE 7: PIN 1. BASE	STYLE 8: PIN 1. GATE	STYLE 9: PIN 1. ANODE	STYLE 10: PIN 1. CATHODE	STYLE 11: PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Docun Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in r	
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

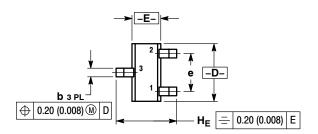
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

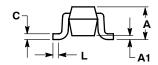




SC-75/SOT-416 **CASE 463** ISSUE G

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. COLLECTOR 3. CATHODE STYLE 4: STYLE 5: PIN 1. CATHODE 2. CATHODE PIN 1. GATE 2. SOURCE

3. DRAIN

#### **GENERIC MARKING DIAGRAM\***

3. ANODE



XX = Specific Device Code

Μ = Date Code = Pb-Free Package

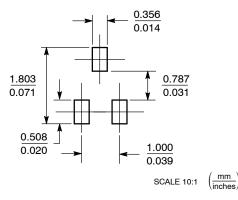
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

#### NOTES

1. DIMENSIONING AND TOLERANCING PER ANSI Y14,5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS				INCHES	;
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
Е	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC		(	0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
He	1.50	1.60	1.70	0.060	0.063	0.067

#### RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from the Document Re Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1

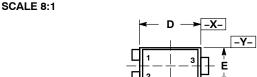
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



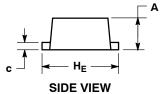


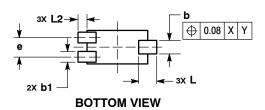
SOT-1123 CASE 524AA ISSUE C

**DATE 29 NOV 2011** 



#### **TOP VIEW**



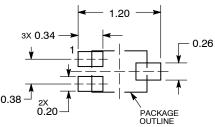


#### NOTES

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				
DIM	MIN MAX				
Α	0.34	0.40			
b	0.15	0.28			
b1	0.10	0.20			
U	0.07	0.17			
D	0.75	0.85			
Е	0.55	0.65			
е	0.35	0.40			
HE	0.95	1.05			
L	0.185 REF				
L2	0.05	0.15			

#### **SOLDERING FOOTPRINT\***



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



Х = Specific Device Code

Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

> STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN STYLE 1: PIN 1. BASE STYLE 2: PIN 1. ANODE STYLE 3: PIN 1. ANODE 2. EMITTER 3. COLLECTOR 2. N/C 3. CATHODE 2. ANODE 3. CATHODE

DESCRIPTION	SOT-1123, 3-LEAD, 1.0x0.6x0.37, 0.35P		PAGE 1 OF 1	
DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		

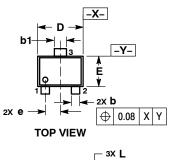
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

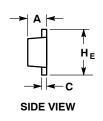


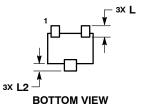


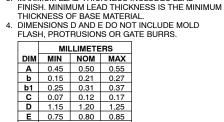
SOT-723 CASE 631AA ISSUE D

**DATE 10 AUG 2009** 









NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME
Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD

NOTES:

ΗE

# RECOMMENDED SOLDERING FOOTPRINT\*

0.40 BSC 1.15 | 1.20 | 1.25

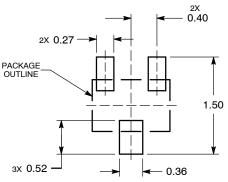
0.15 0.20 0.25





XX = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURC
2 COLLECTOR	2 CATHODE	2 CATHODE	2 ANODE	2 DDAIN

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Re Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-723		PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems. or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales